

Towards Trusted Devices in FPGA by Modeling Radiation Induced Errors

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Problem definition



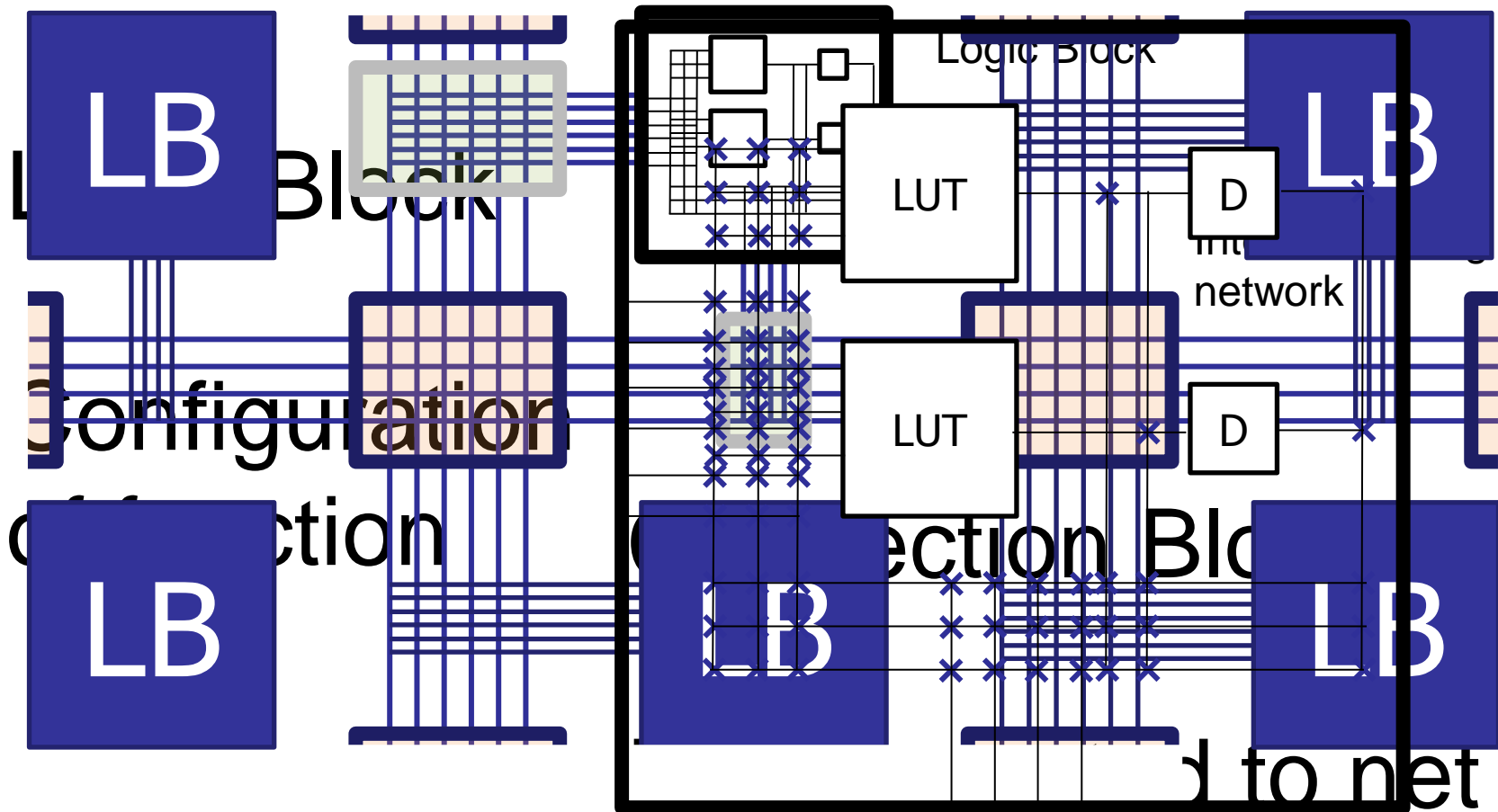
■ FPGA

- Programmable logic device
- Lot of memory cells
 - Logic functions and interconnection - Configuration
 - D Flip-flops for sequential logic - Data

Hierarchy of FPGA interconnection



Switch blocks – global connections

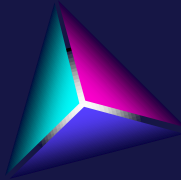




Problem definition



- **FPGA**
 - Programmable logic device
 - Lot of memory cells
 - Logic functions and interconnection - Configuration
 - D Flip-flops for sequential logic - Data
- **CMOS**
 - Small structures
 - Controlled by voltage
- **Ionizing radiation**
 - Transferring energy through matter
 - Depositing charge → inducing current → voltage change
- **Problem: Single-event effects (SEE), mainly upsets (SEU)**



SEU in FPGA



- Change of
 - Function (LUT)
 - Structure (interconnection)
 - Data (D-FF)
- Locally unpredictable – can hit any location
- Can influence dependability of the circuit/application
- But fightable by
 - Redundancy
 - Self check
 - Self repair (reconfiguration, ECC, ...)
- Need of quantitative characteristic



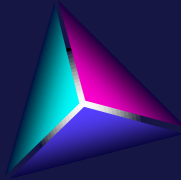
Quantitative characteristic



- Deep simulation to the level of CMOS technology
 - Unusable for real system – size

- Accelerated life testing (ALT)
 - Unusable for real system – too specific, too expensive

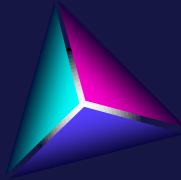
- Combination?
 - Partial simulation
and
 - Partial ALT



Proposed Method



1. Create quantitatively described platform model
 - a) Based on higher-level simulation
 - b) Calibrated by Accelerated Life Tests
2. Use the model to predict any future design's behavior on this platform

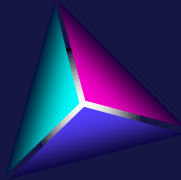


Proposed Method



- a) Higher-level simulation
 - Based on VTR framework
 - Custom FPGA architecture
 - Timing-driven place-n-route on given platform
 - Defect injection
 - Fault simulation

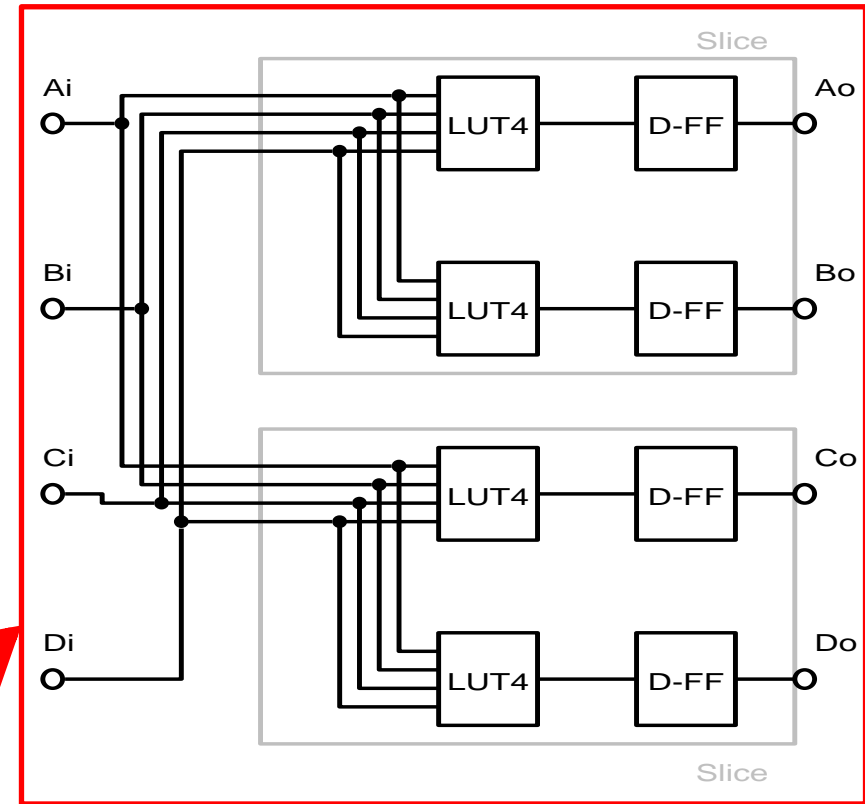
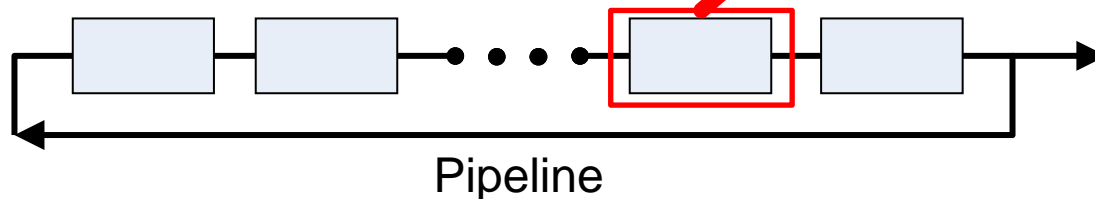
- a) Calibration by Accelerated Life Tests
 - Only on several special designs
 - Only for model calibration



Test Circuit Example



- Tests all LUTs and flip-flops
- Propagates any error to output
- Forms a long pipeline
- Is preloaded with data upon flip-flops reset
- Detects fault rate on the particular device under particular conditions



One pipeline stage



Test Circuit Example – Code



- Symmetric
- After odd number of conversions, the output is same as input
- Any bit flip in any LUT appears as a change in the sequence

Code 1	Code 2
0000	1001
0001	1010
0010	1111
0011	0110
0100	0011
0101	0111
0110	1100
0111	0101

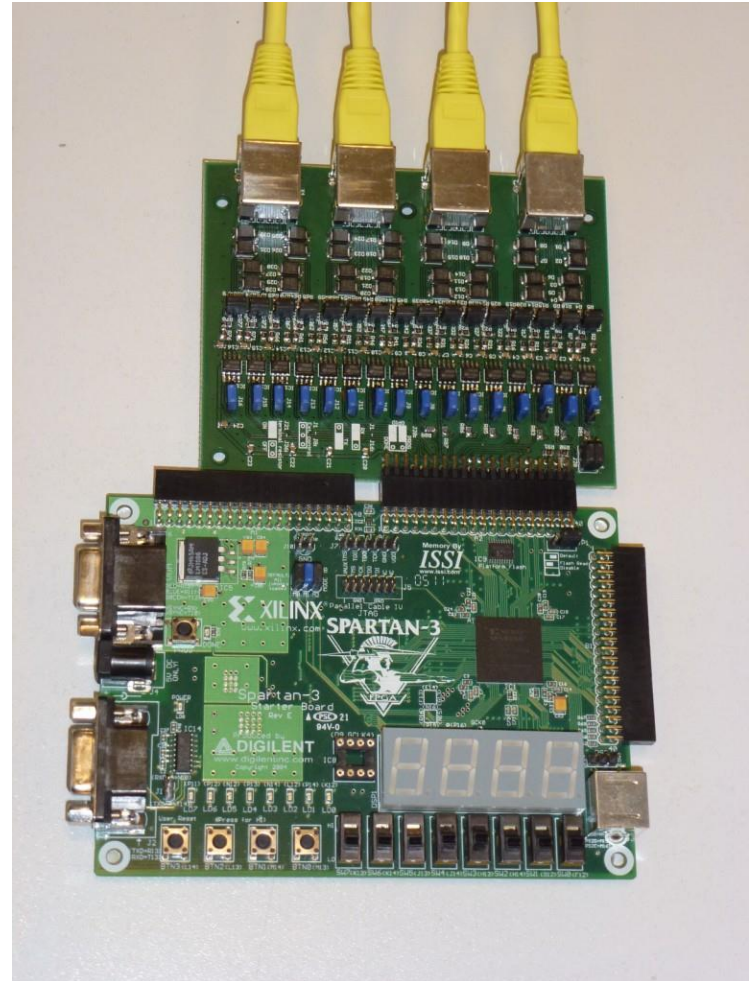
Code 1	Code 2
1000	1011
1001	0000
1010	0001
1011	1000
1100	0110
1101	1110
1110	1101
1111	0010



Entire Test System

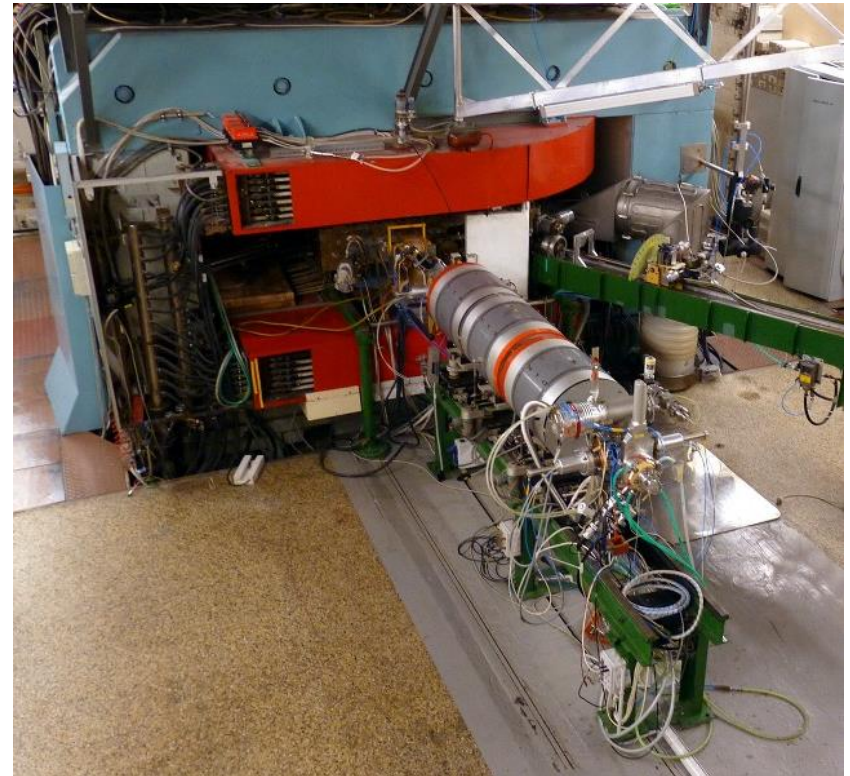


- Based on Spartan 3 Starter Kits
- Two parts
 - One under radiation
 - One away from radiation
- Connected through 16 differential lines
- Radiated part is controlled from the shielded one
 - Remote monitoring, reset, reload





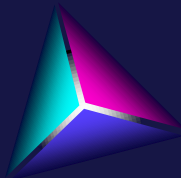
- Isochronous cyclotron U-120M
- At NPI Řež, ASCR
- Up to 37 MeV protons
- Intensity from 10^4 p/cm²/s





Irradiation Setup





Irradiation Setup

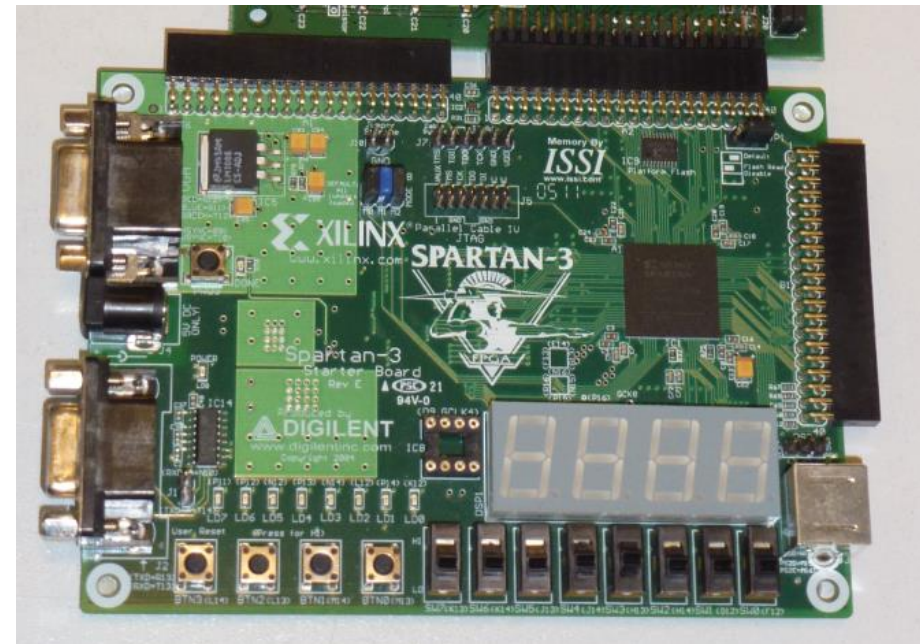


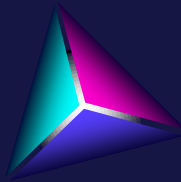


Spartan3 Irradiation



- Xilinx SRAM FPGA
- Starter Kit used
 - XC3S200 device
- 90 nm CMOS technology
- Only SEU in configuration memory (CMem) counted

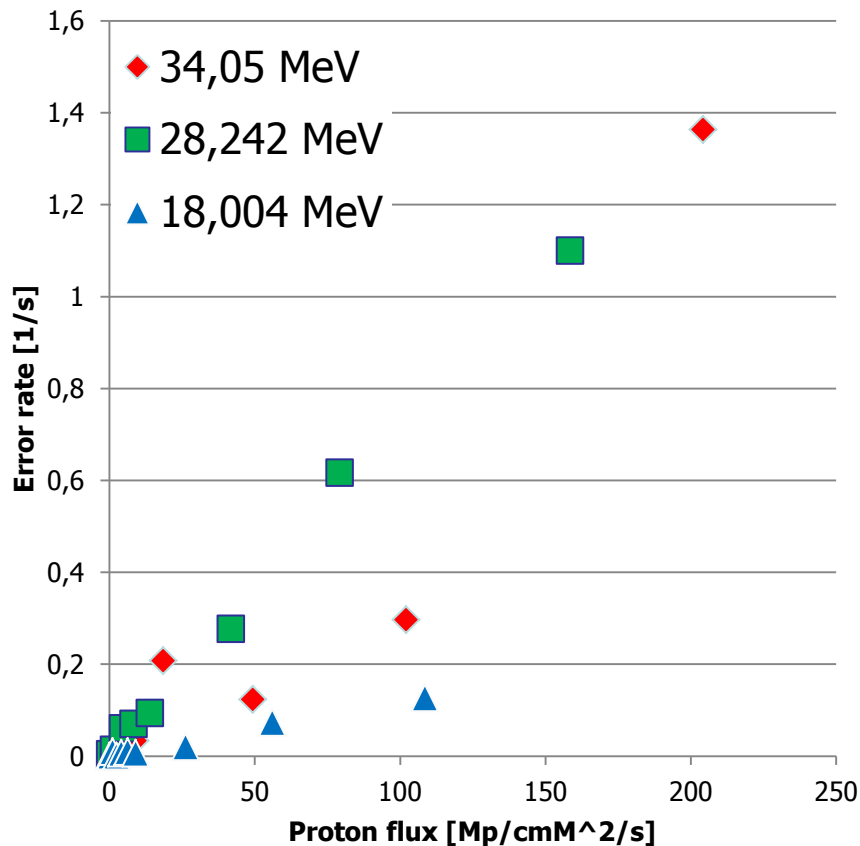




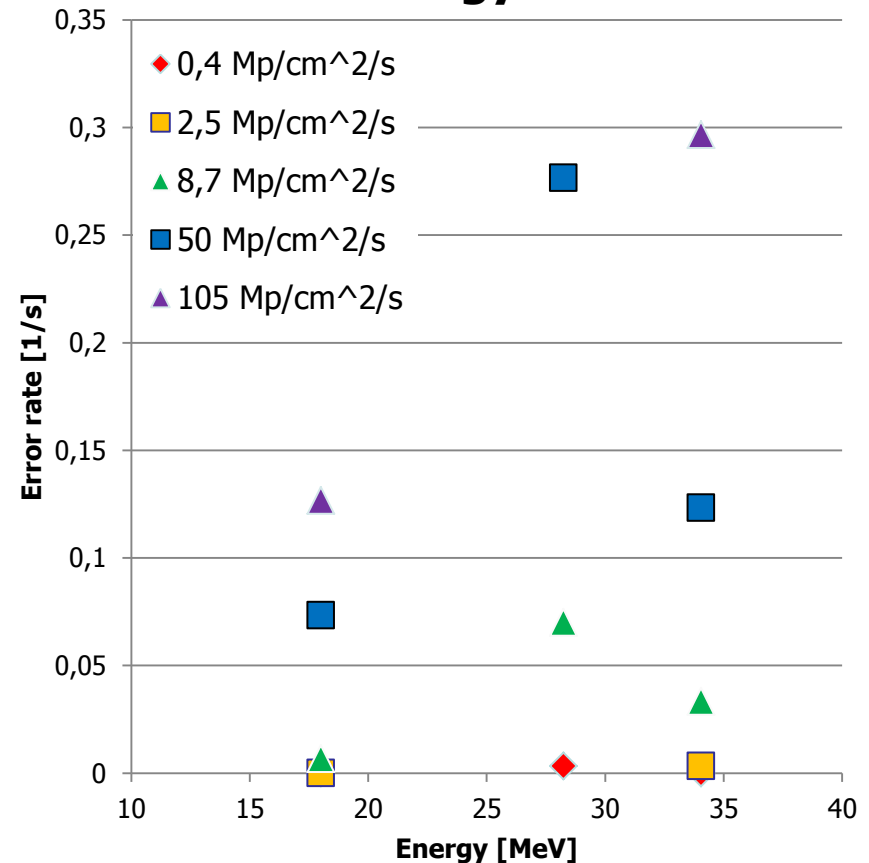
Spartan3 Irradiation



Configuration error rate vs. proton flux



Configuration error rate vs. energy

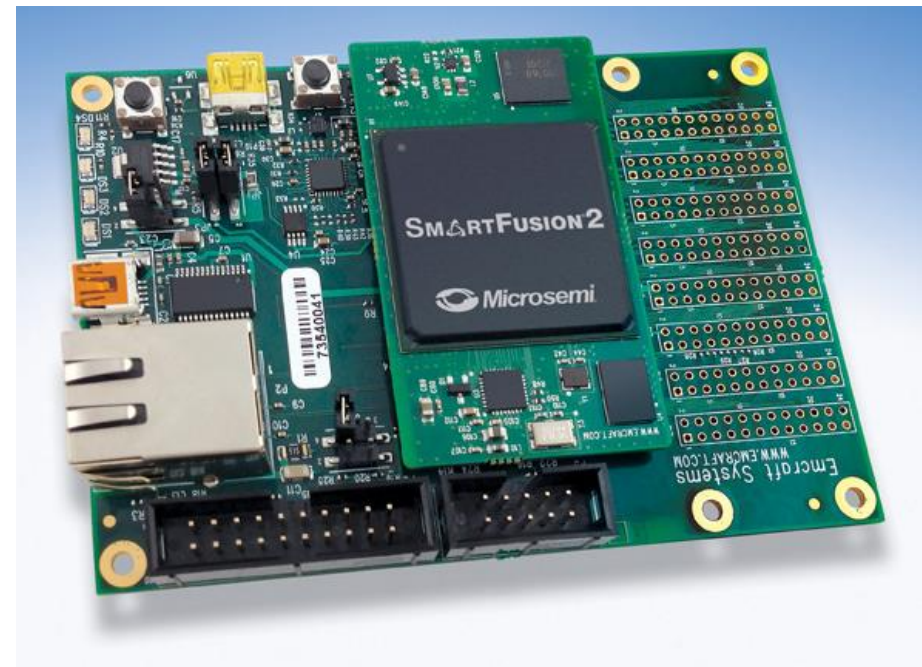




SmartFusion2 Irradiation



- Microsemi FLASH SoC
 - Only FPGA part tested
- Starter Kit used
 - M2S050-FGG484 device
- 65 nm CMOS technology
- No SEU in configuration memory
- Some SEU in “data” flip-flops (D-FFs)

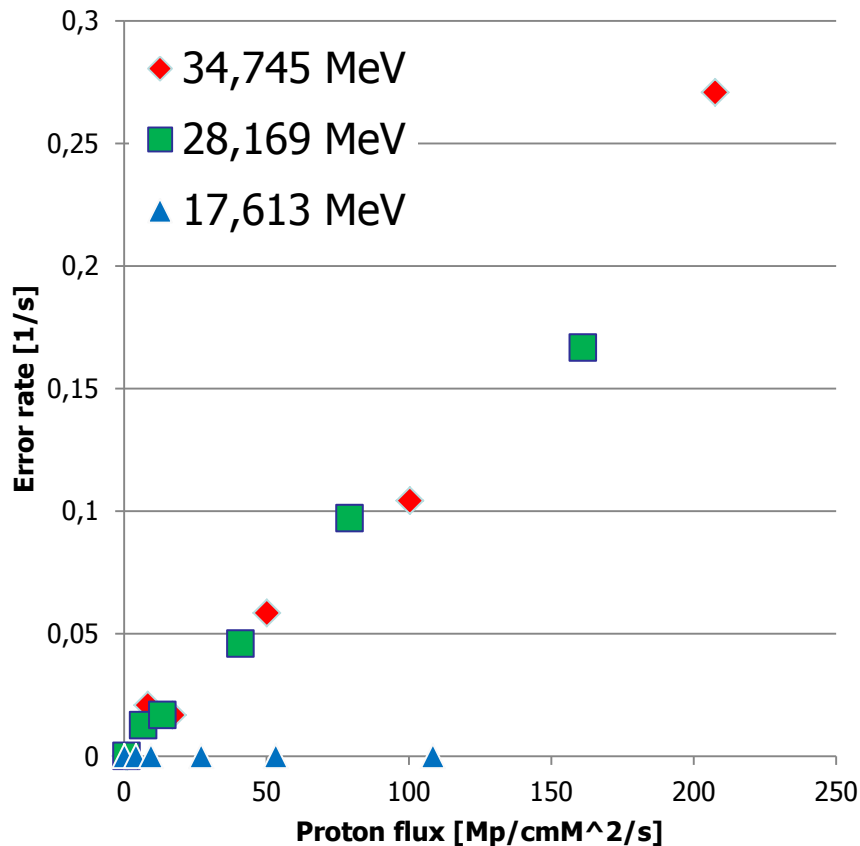




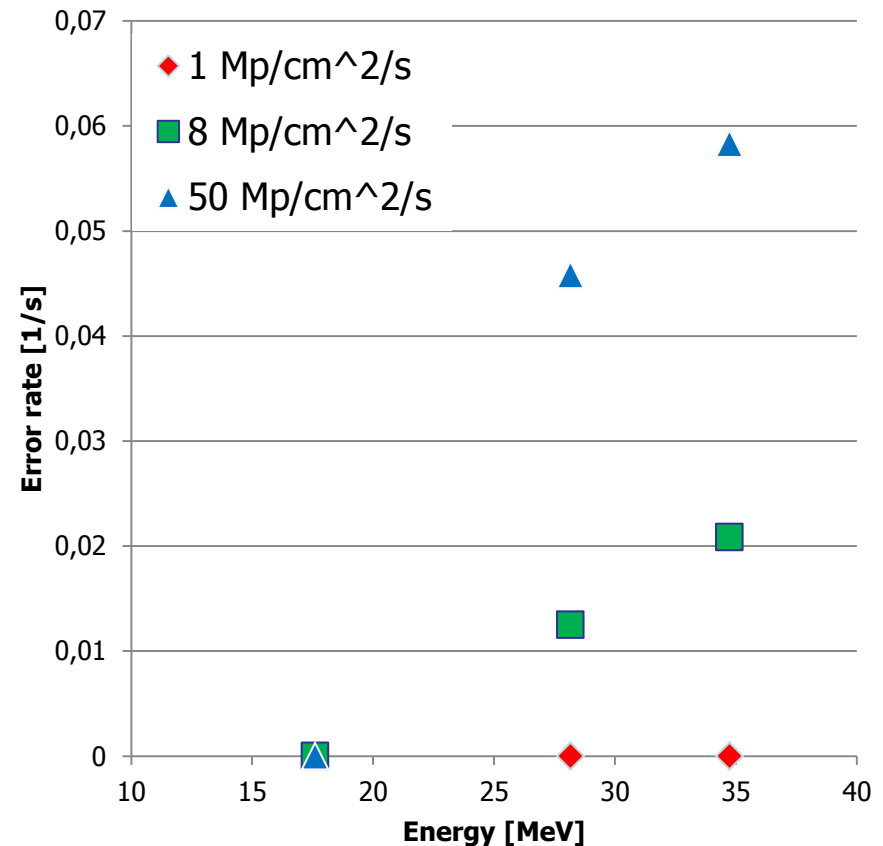
SmartFusion2 Irradiation



D-FF error rate vs. proton flux



D-FF error rate vs. energy





Current work



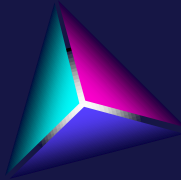
- Preparing the same test for the IGLOO2 FLASH based FPGA
- Precise monitoring of the total dose
- Upgrade the communication module
- Synchronization of the FPGAs clock with cyclotron frequency
- Improving model of architecture, collect another data and calibrate the model



Conclusions



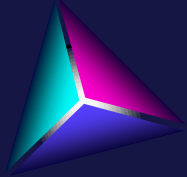
- We have proposed **new method** for predicting quantitative characteristics of **SEU sensitivity** of **digital circuits** implemented in **FPGA**.
- We have completed the first runs of ALT.
- We are currently working on the simulation model, improving the ALT system and preparing the tests for other devices.
- This method can be used for verifying **dependability** and **security** parameters of various designs implemented in **FPGA**



Conclusions



- FLASH based SmartFusion 2 (65 nm) has better resistance to Single Event Effects than Spartan 3 (90 nm)
 - Configuration memory completely safe
 - D flip-flops less vulnerable, although it is a smaller technology
- But the SmartFusion 2 has a very low total ionizing dose to permanently destroy to destroy the FLASH programming controller.
 - ~4 kRads for SF2
 - Spartan 3 already survived several hundreds of kRads without permanent error noticed



Digital Design and Dependability Research Group

FIT, CTU in Prague



Thank you!

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